

### INCHANGE SEMICONDUCTOR

# isc N-Channel MOSFET Transistor

# **IRFU120**

#### FEATURES · Static drain-source on-resistance: 2.Drain Ros(on)≤0.27Ω · Enhancement mode 100% avalanche tested 1.Gate Minimum Lot-to-Lot variations for robust device Source performance and reliable operation DESCRITION Power factor correction IPAK TO-251 Package Switched mode power supplies ABSOLUTE MAXIMUM RATINGS(Ta=25°C) SYMBOL PARAMETER VALUE UNIT C V 100 VDSS Drain-Source Voltage Nγ $V_{GS}$ Gate-Source Voltage $\pm 20$ D **Drain Current-Continuous** 7.7 А $I_D$ Drain Current-Single Pulsed **I**DM 31 А F J G $P_{D}$ Total Dissipation @Tc=25°C 42 W mm Max. Operating Junction Temperature 150 °C Tj DIM MIN MAX 6.35 6.45 A B 5.20 5.40 Storage Temperature -55~150 °C Tstg 5.30 5.50 c D 8.00 8.20 2.30 2.50 E F 0.50 0.60

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#### THERMAL CHARACTERISTICS

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SYMBOL	PARAMETER	МАХ	UNIT	
Rth(j-c)	Channel-to-case thermal resistance	2.98	°C <b>/W</b>	

2.10

4.15

0.40

0.70

1.40

0.55

G н

J

κ

L

N

2.40

4.45

0.60

0.90

1.60

0.65

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#### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A	100			V
$V_{GS(th)}$	Gate Threshold Voltage	VDS=VGS; I <sub>D</sub> =250	2		4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =4.6A			0.27	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V; V <sub>DS</sub> =0V			±100	nA
loss	Drain-Source Leakage Current	V <sub>DS</sub> =100V; V <sub>GS</sub> = 0V			25	μΑ
		V <sub>DS</sub> =80V; V <sub>GS</sub> = 0V; T <sub>j</sub> =125°C			250	
V <sub>SD</sub>	Diode forward voltage	I <sub>SD</sub> = 7.7A, V <sub>GS</sub> = 0V			2.5	V

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